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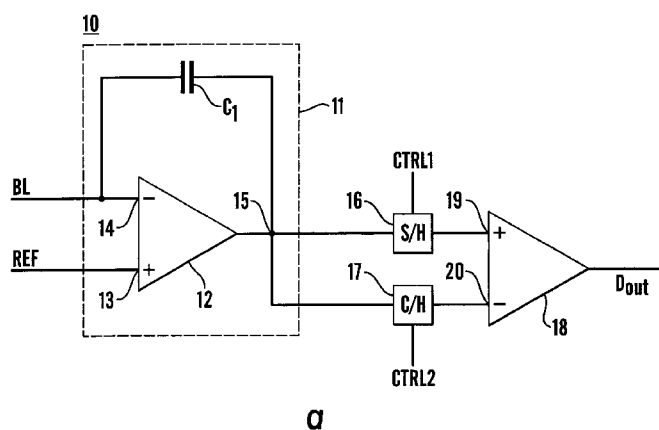
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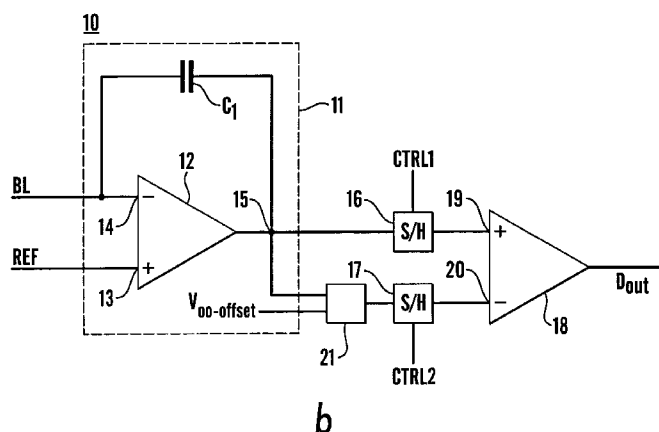
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(54) Title: SENSING DEVICE FOR A PASSIVE MATRIX MEMORY AND A READ METHOD FOR USE THEREWITH



(57) Abstract: A sensing device (10) for reading data stored in a passive matrix memory comprising memory cells in the form of ferroelectric capacitors, comprises an integrator circuit (11) for sensing the current response and means (16, 17, 18) for storing and comparing two consecutive read values, one of which is a reference value. In a read method for use with the sensing device a bit line is connected to the sensing device for sensing a charge flowing therebetween and a memory cell at the crossing of the former and an activated word line, whereafter two consecutive reads of the memory cell are performed an integrated over predetermined time periods in order to generate first and second read values which are compared for determining a logical value dependent on the sensed charge.



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